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A METHOD TO FABRICATE A STRAINED Si CMOS STRUCTURE USING SELECTIVE EPITAXIAL DEPOSITION OF Si AFTER DEVICE ISOLATION FORMATION

ABSTRACT OF THE DISCLOSURE

A strained Si CMOS structure is formed by steps which include forming a relaxed SiGe layer (12) on a surface of a substrate (10); forming isolation regions (14) and well implant regions (16) in said relaxed SiGe layer (12); and forming a strained Si layer (18) on said relaxed SiGe layer (12). These processing steps may be used in conjunction with conventional gate processing steps in forming a strained MOSFET structure.

Fig. 3



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